

Silicon PNP Power Transistors

2N6229 2N6230 2N6231

DESCRIPTION

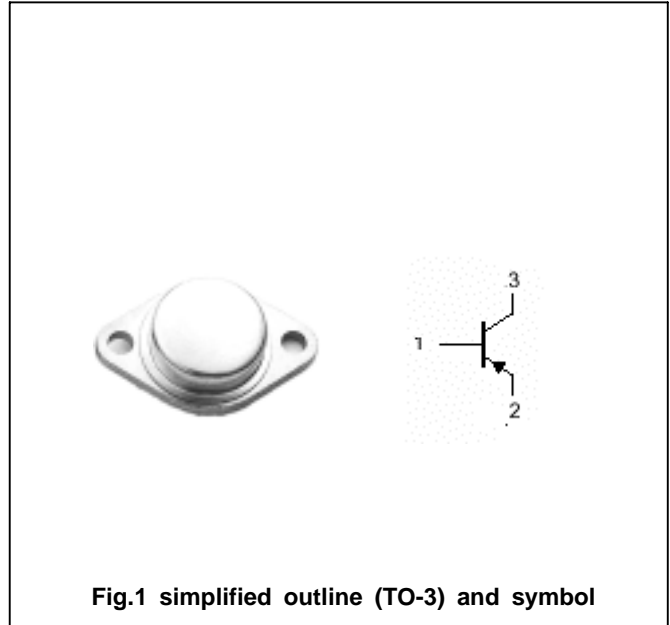
- With TO-3 package
- Low collector saturation voltage
- Excellent safe operating area

APPLICATIONS

- For high power audio; disk head positioners and other linear applications.

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6229	100	V
		2N6230	120	
		2N6231	140	
V _{CEO}	Collector-emitter voltage	2N6229	100	V
		2N6230	120	
		2N6231	140	
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		10	A
P _D	Total power dissipation	T _C =25	150	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	0.875	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter sustaining voltage	2N6229	I _C =0.2A ; I _B =0	100			V
		2N6230		120			
		2N6231		140			
V _{CEsat}	Collector-emitter saturation voltage		I _C =4A ; I _B =0.4A			1.0	V
V _{BE}	Base-emitter on voltage		I _C =5A ; V _{CE} =2V			2.0	V
I _{CEO}	Collector cut-off current		V _{CE} =Rated V _{CEO} ; I _B =0			5.0	mA
I _{CBO}	Collector cut-off current		V _{CB} =Rated V _{CBO} ; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current		V _{EB} =7V ; I _C =0			0.1	mA
h _{FE}	DC current gain	2N6229	I _C =5A ; V _{CE} =2V	25		100	
		2N6230		20		80	
		2N6231		15		60	
f _T	Transition frequency		I _C =0.5A ; V _{CE} =4V	1			MHz

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PACKAGE OUTLINE

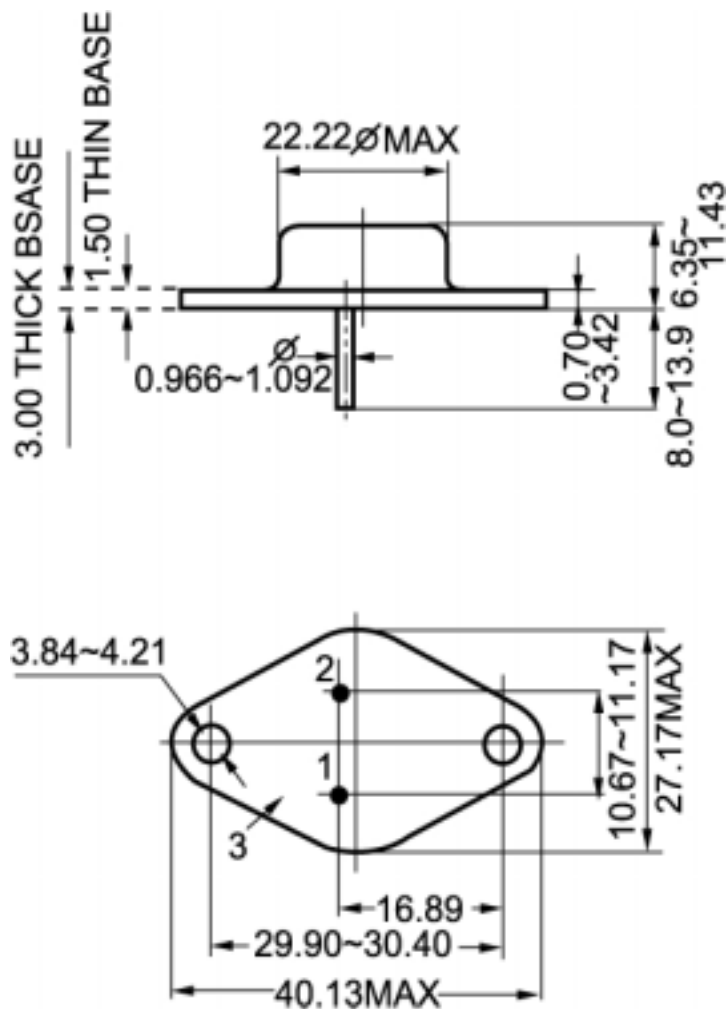


Fig.2 outline dimensions (unindicated tolerance: ± 0.1 mm)